

# UNISONIC TECHNOLOGIES CO., LTD

2SK3557 **Preliminary JFET** 

# FIELD EFFECT TRANSISTOR SILICON N-CHANNEL JUNCTION TYPE

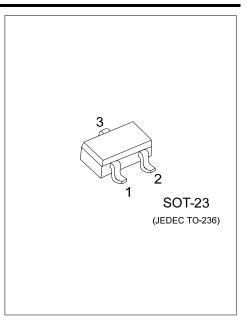
#### DESCRIPTION

The UTC 2SK3557 is an N-channel junction silicon FET, it uses UTC's advanced technology to provide the customers with low I<sub>GSS</sub> and low C<sub>RSS</sub>.

The UTC 2SK3557 is suitable for audio frequency low noise amplifier, impedance conversion, infrared sensor applications.

#### **FEATURES**

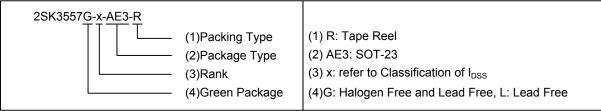
- \* Small Ciss
- \* Ultralow Noise Figure
- \* High breakdown voltage: V<sub>GDS</sub>=-15V
- \* High input impedance: I<sub>GSS</sub>=-1nA (max) at V<sub>GS</sub>=-10V



#### ORDERING INFORMATION

Ordering	Number	Deelrane	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2SK3557L-x-AE3-R	2SK3557G-x-AE3-R	SOT-23	S	D	G	Tape Reel	

Note: Pin Assignment: S: Source D: Drain G: Gate



#### **MARKING**



# ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSX}$	15	V
Gate-Drain Voltage	$V_{GDS}$	-15	V
Gate Current	$I_{G}$	10	mA
Drain Current	I <sub>D</sub>	50	mA
Power Dissipation	$P_{D}$	200	mW
Junction Temperature	TJ	+150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ +125	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS			ā.	ā.		
Gate Cut-off Current	I <sub>GSS</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =0V			-1.0	nA
Gate-Drain Breakdown Voltage	V <sub>(BR)GDS</sub>	I <sub>G</sub> =-10μA, V <sub>DS</sub> =0V	-15			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =5V, V <sub>GS</sub> =0V	10		32	mA
Forward Transfer Admittance	yfs	V <sub>DS</sub> =5V, V <sub>GS</sub> =0V, f=1kHz	24	35		mS
ON CHARACTERISTICS					_	
Cutoff Voltage	V <sub>GS(OFF)</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =100μA	-0.3	-0.7	-1.5	V
DYNAMIC PARAMETERS					_	
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =5V, V <sub>GS</sub> =0V, f=1MHz		12		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>	V <sub>DG</sub> =5V, I <sub>D</sub> =0A, f=1MHz		6		Pf
Noise Figure	NF	$V_{DG}$ =5V, $R_G$ =1k $\Omega$ , $I_D$ =1mA, f=1MHz		1		dB

# CLASSIFICATION OF I<sub>DSS</sub>

RANK	6	7
RANGE	10 ~ 20	16 ~ 32

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